

L Number	Hits	Search Text	DB	Time stamp
3	5	wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same ratio same sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 16:11
4	39	(sapphire adj substrate) with (metal adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 16:12
5	168	wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4) with sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:12
8	0	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4)) and ((thermoplastic with liquid) with heating with solid)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:15
9	0	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4)) and (((thermoplastic with liquid) with heating) same solid)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:15
10	0	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4)) and (((thermoplastic with liquid) with heating) same solid\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:16
6	124	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4)) and (thermoplastic with liquid)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:17
7	7	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4)) and ((thermoplastic with liquid) with heating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:21
11	27	(thermoplastic with liquid with heating) same (solid adj thermoplast\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:24
12	27	(thermoplastic with liquid with heating) same (solid adj thermoplast\$4) same heat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:24
13	2	(thermoplastic with liquid with heating) same (solid adj thermoplast\$4) same press\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 17:25
-	0	((sapphire adj substrate) with (metal adj layer)) and (plasma near2 etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 14:26

-	2	((sapphire near2 substrate) same (metal adj layer)) and (plasma near2 etch\$4)) and (metal with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 15:10
-	2	("6586315").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 15:27
-	4	((("6586315") or ("6551906"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 17:03
-	1		USPAT	2004/08/06 15:28
-	1		USPAT	2004/08/06 15:28
-	6	((("6586315") or ("6551906") or ("20020178883"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 17:05
-	198	wafer same dic\$4 same sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:28
-	0	wafer with (pars\$4 or saw\$4 or dic\$4) with sapphire with cool\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 17:09
-	72	wafer with (pars\$4 or saw\$4 or dic\$4) with sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 17:19
-	26	(wafer with (pars\$4 or saw\$4 or dic\$4) with sapphire) and cool\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 09:00
-	72	(conduct\$4 adj layer) with pattern\$4 with dielectric with cap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 10:33
-	26	((sapphire near2 substrate) same (metal adj layer)) and (plasma near2 etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:21
-	177	(sapphire near2 substrate) same (metal adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:23
-	5	wafer same (dic\$4 or cut\$4 or pars\$4) same ratio same sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:38

-	183	wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:24
-	16	wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4) with (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:43
-	16	wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4) with (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 13:49
-	16	(wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4) with (aspect adj ratio)) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:05
-	4	((wafer with (dic\$4 or cut\$4 or pars\$4 or saw\$4) with (aspect adj ratio)) and (aspect adj ratio)) and sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:05
-	4	wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same (low adj aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:25
-	4	(wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same (low adj aspect adj ratio)) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:26
-	4	(wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same (low adj aspect adj ratio)) and (low adj aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:28
-	9	(wafer same (dic\$4 or cut\$4 or pars\$4 or saw\$4) same (aspect adj ratio)) and (low adj aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 14:28